

Power transistor (60V, 3A)

• Features

- 1) High speed switching. (Tf : Typ. : 30ns at IC = 3A)
- 2) Low saturation voltage, typically (Typ. : 200mV at IC = 2A, IB = 200mA)
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SA2071.

• Applications

NPN Silicon epitaxial planar transistor

• Structure

Low frequency amplifier High speed switching

• Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	VCBO	60	V
Collector-emitter voltage	VCEO	60	V
Emitter-base voltage	VEBO	6	V
Collector current	IC	3	A
	ICP	6	A *1
Power dissipation	PC	500	mW *2
	PC	2.0	W *3
Junction temperature	Tj	150	°C
Range of storage temperature	Tstg	-55~+150	°C

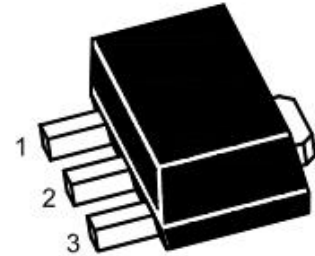
*1 Pw=100ms

*2 Each terminal mounted on a recommended land.

*3 Mounted on a 40x40x0.7(mm) ceramic substrate

• hFE RANK

Q	R
120-270	180-390



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

Marking:5824Q/R

• **Electrical characteristics (Ta=25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	60	–	–	V	IC=100μA
Collector-emitter breakdown voltage	BVCEO	60	–	–	V	IC=1mA
Emitter-base breakdown voltage	BVEBO	6	–	–	V	IE=100μA
Collector cut-off current	ICBO	–	–	1.0	μA	VCB=40V
Emitter cut-off current	IEBO	–	–	1.0	μA	VEB=4V
Collector-emitter saturation voltage	VCE(sat)	–	200	500	mV	IC=2A, IB=200mA *1
DC current gain	hFE	120	–	390	–	VCE=2V, IC=100mA
Transition frequency	fT	–	200	–	MHz	VCE=10V, IE=–100mA, f=10MHz *
Collector output capacitance	Cob	–	20	–	pF	VCB=10V, IE=0mA, f=1MHz
Turn-on time	Ton	–	50	–	ns	IC=3A, IB1=300mA, IB2=–300mA, VCC 25V *2
Storage time	Tstg	–	150	–	ns	
Fall time	Tf	–	30	–	ns	

*1 Non repetitive pulse
*2 See switching characteristics measurement circuits

• **Electrical characteristic curves**

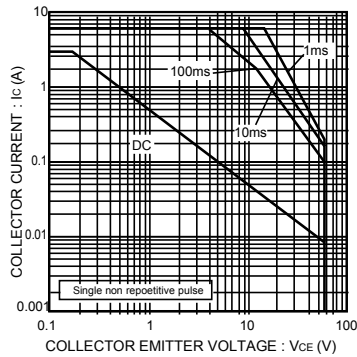


Fig.1 Safe operating area

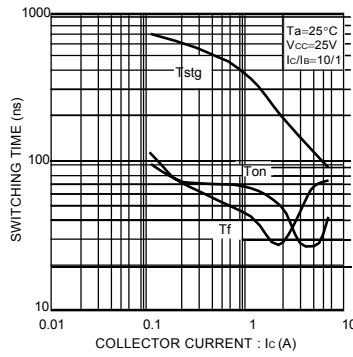


Fig.2 Switching Time

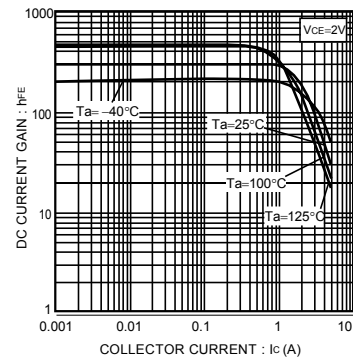


Fig.3 DC current gain vs. collector current

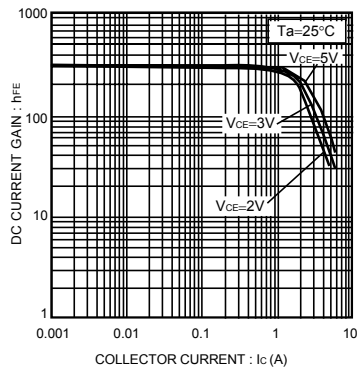


Fig.4 DC current gain vs. collector current

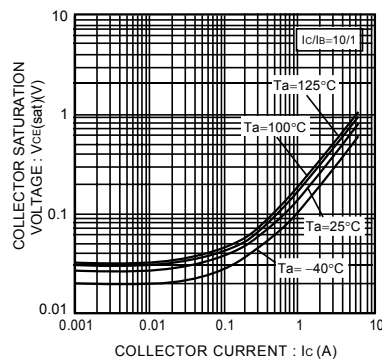


Fig.5 Collector-emitter saturation voltage vs. Collector Current

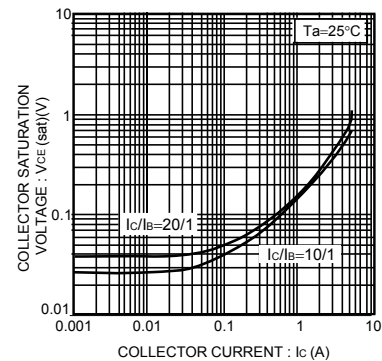


Fig.6 Collector-emitter saturation voltage vs. collector current

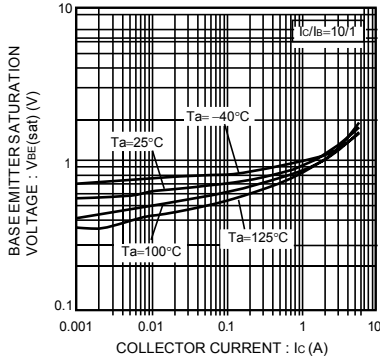


Fig.7 Base-emitter saturation voltage vs. collector current

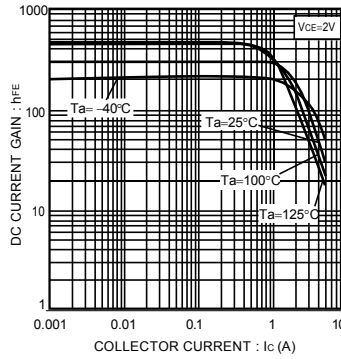


Fig.3 DC current gain vs. collector current

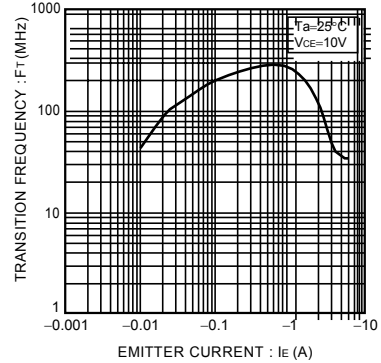


Fig.9 Transition frequency

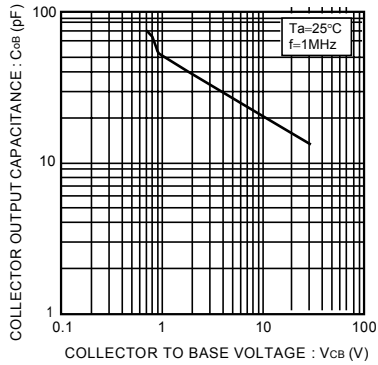
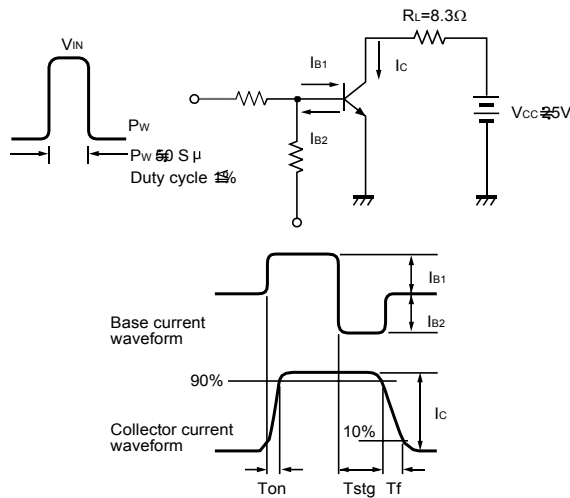
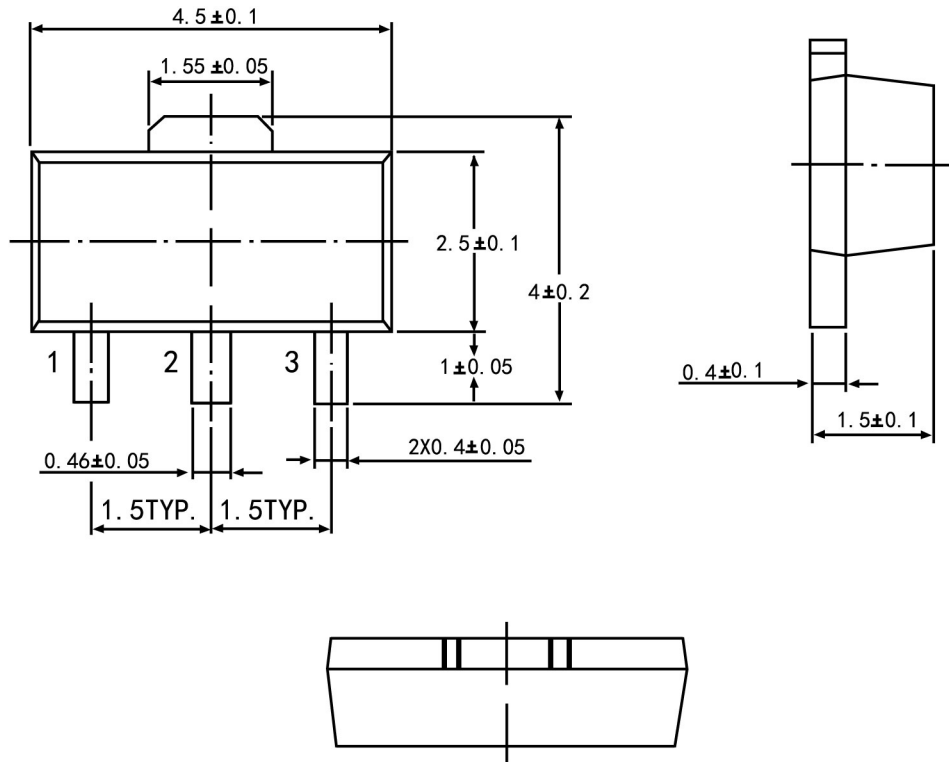


Fig.10 Collector output capacitance

• Switching characteristics measurement circuits



SOT-89 PACKAGE OUTLINE



Symbol	Dimension in Millimeters	
	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.44
D	4.40	4.60
D1	1.62	1.83
E	2.29	2.60
e	1.50 Typ	
H	3.94	4.25
H1	2.63	2.93
L	0.89	1.20
All Dimensions In mm		